SCES325G - JULY 2001 - REVISED SEPTEMBER 2003

- **Available in the Texas Instruments** NanoStar™ and NanoFree™ Packages
- 1.65-V to 5.5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 0.8 ns at 3.3 V
- **High On-Off Output Voltage Ratio**
- **High Degree of Linearity**
- High Speed, Typically 0.5 ns $(V_{CC} = 3 V, C_{L} = 50 pF)$
- Rail-to-Rail Input/Output
- Low On-State Resistance, Typically \approx 6 Ω $(V_{CC} = 4.5 V)$
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II

DCT OR DCU PACKAGE (TOP VIEW) 8 NCC 1A [1 1C 1B **∏** 2 7 6 🛮 2B 2C 🛮 3 GND [Π2A

YEA, YEP, YZA, OR YZP PACKAGE (BOTTOM VIEW)

			1
GND	04	50	2A
2C	○3	6 O 7 O	2B
1B	O 2	70	1C
1A	01	80	V_{CC}

description/ordering information

This dual bilateral analog switch is designed for 1.65-V to 5.5-V $\rm V_{CC}$ operation.

The SN74LVC2G66 can handle both analog and digital signals. The device permits signals with amplitudes of up to 5.5 V (peak) to be transmitted in either direction.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Each switch section has its own enable-input control (C). A high-level voltage applied to C turns on the associated switch section.

ORDERING INFORMATION

TA	PACKAGE [†]	ORDERABLE PART NUMBER	TOP-SIDE MARKING‡	
	NanoStar™ – WCSP (DSBGA) 0.17-mm Small Bump – YEA		SN74LVC2G66YEAR	
−40°C to 85°C	NanoFree™ – WCSP (DSBGA) 0.17-mm Small Bump – YZA (Pb-free)	D 1 (0000	SN74LVC2G66YZAR	00
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP	Reel of 3000	SN74LVC2G66YEPR	C6_
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)		SN74LVC2G66YZPR	
	SSOP - DCT	Reel of 3000	SN74LVC2G66DCTR	C66
	Vecop pour	Reel of 3000	SN74LVC2G66DCUR	Cee
	VSSOP – DCU	Reel of 250	SN74LVC2G66DCUT	C66_

[†]Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site. DCU: The actual top-side marking has one additional character that designates the assembly/test site. YEA/YZA, YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NanoStar and NanoFree are trademarks of Texas Instruments.



SCES325G - JULY 2001 - REVISED SEPTEMBER 2003

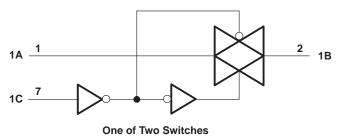
description/ordering information (continued)

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

FUNCTION TABLE (each section)

CONTROL INPUT (C)	SWITCH
L	Off
Н	On

logic diagram, each switch (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC} (see Note 1)		–0.5 V to 6.5 V
Input voltage range, V _I (see Notes 1 and 2)		–0.5 V to 6.5 V
Switch I/O voltage range, V _{I/O} (see Notes 1, 2,	and 3)	$-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Control input clamp current, I _{IK} (V _I < 0)		
I/O port diode current, I_{IOK} ($V_{I/O} < 0$ or $V_{I/O} > V$	V _{CC})	±50 mA
On-state switch current, $I_T (V_{I/O} = 0 \text{ to } V_{CC})$		±50 mA
Continuous current through V _{CC} or GND		±100 mA
Package thermal impedance, θ _{JA} (see Note 4):	DCT package	220°C/W
-	DCU package	227°C/W
	YEA/YZA package	140°C/W
	YEP/YZP package	102°C/W
Storage temperature range, T _{stg}		–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltages are with respect to ground unless otherwise specified.
 - 2. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 3. This value is limited to 5.5 V maximum.
 - 4. The package thermal impedance is calculated in accordance with JESD 51-7.



SN74LVC2G66 DUAL BILATERAL ANALOG SWITCH

SCES325G - JULY 2001 - REVISED SEPTEMBER 2003

recommended operating conditions (see Note 5)

			MIN	MAX	UNIT
Vcc	Supply voltage		1.65	5.5	V
V _{I/O}	I/O port voltage		0	VCC	V
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	V _{CC} × 0.65		
	LPak lavel Sand vellage as a sected Sand	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	V _{CC} ×0.7		.,
VIH	High-level input voltage, control input	V _{CC} = 3 V to 3.6 V	V _{CC} ×0.7		V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	V _{CC} ×0.7		
	Low-level input voltage, control input	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		V _{CC} × 0.35	
Mari		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		$V_{CC} \times 0.3$	V
VIL		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		$V_{CC} \times 0.3$	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$V_{CC} \times 0.3$	
٧ _I	Control input voltage		0	5.5	V
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		20	
44/4	hands the neiting view (fall time	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		20	0/
Δt/Δv	Input transition rise/fall time	V _{CC} = 3 V to 3.6 V		10	ns/V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		10	
TA	Operating free-air temperature		-40	85	°C

NOTE 5: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

SCES325G - JULY 2001 - REVISED SEPTEMBER 2003

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST COND	TEST CONDITIONS			MAX	UNIT
			$I_S = 4 \text{ mA}$	1.65 V	12.5	30	
_		$V_I = V_{CC}$ or GND,	$I_S = 8 \text{ mA}$	2.3 V	9	20	
ron	On-state switch resistance	VC = VIH (see Figures 1 and 2)	I _S = 24 mA	3 V	7.5	15	Ω
		,	I _S = 32 mA	4.5 V	6	10	
			I _S = 4 mA	1.65 V	85	120	
	Beel, on etate resistance	$V_I = V_{CC}$ to GND,	I _S = 8 mA	2.3 V	22	30	
ron(p)	Peak on-state resistance	V _C = V _{IH} (see Figures 1 and 2)	I _S = 24 mA	3 V	12	20	Ω
		,	$I_S = 32 \text{ mA}$	4.5 V	7.5	15	
			I _S = 4 mA	1.65 V		7	
	Difference of on-state resistance between switches	$V_I = V_{CC}$ to GND, $V_C = V_{IH}$ (see Figures 1 and 2)	I _S = 8 mA	2.3 V		5	Ω
Δr_{on}			I _S = 24 mA	3 V		3	
		,	I _S = 32 mA	4.5 V		2	
		V _I = V _{CC} and V _O = GND				±1	
IS(off)	Off-state switch leakage current	f-state switch leakage current $V_I = GND$ and $V_O = V_{CC}$, $V_C = V_{IL}$ (see Figure 3)	5.5 V		±0.1†	μΑ	
lo()	On-state switch leakage current	$V_I = V_{CC}$ or GND, $V_C =$	V _{IH} , V _O = Open	5.5 V		±1	μА
^I S(on)	On-state switch leakage current	(see Figure 4)		3.5 V		±0.1 [†]	μΛ
11	Control input current	V _C = V _C C or GND		5.5 V		±1	μА
-1		10 100 1111				±0.1 [†]	P** 1
Icc	Supply current	0 00		5.5 V		10	μΑ
	Cappi, canoni					1†	p
∆ICC	Supply-current change	$V_C = V_{CC} - 0.6 V$		5.5 V		500	μΑ
C _{iC}	Control input capacitance			5 V	3.5		pF
C _{io(off)}	Switch input/output capacitance				6		pF
C _{io(on)}	Switch input/output capacitance			5 V	14		pF

 $[†]T_A = 25^{\circ}C$

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figure 5)

PARAMETER	FROM	TO (OUTPUT)	V _{CC} = ± 0.1		V _{CC} =		V _{CC} =		V _{CC} =		UNIT
	(INPUT) (OUTPUT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd} ‡	A or B	B or A		2		1.2		8.0		0.6	ns
t _{en} §	С	A or B	2.3	10	1.6	5.6	1.5	4.4	1.3	3.9	ns
t _{dis} ¶	С	A or B	2.5	10.5	1.2	6.9	2	7.2	1.1	6.3	ns

[‡] tpLH and tpHL are the same as tpd. The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).



[§] tpzL and tpzH are the same as ten.

[¶] tpLZ and tpHZ are the same as tdis.

analog switch characteristics, $T_{\mbox{\scriptsize A}}$ = 25 $^{\circ}\mbox{\scriptsize C}$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	vcc	TYP	UNIT
				1.65 V	35	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	120	
			f _{in} = sine wave (see Figure 6)	3 V	175	
Frequency response†	A == D	D on A	(000 : 1941.0 0)	4.5 V	195	NAL I—
(switch on)	A or B	B or A		1.65 V	>300	MHz
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	>300	
			f _{in} = sine wave (see Figure 6)	3 V	>300	
			(868 : 1941.6 6)	4.5 V	>300	
				1.65 V	-58	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	-58	
			f _{in} = 1 MHz (sine wave) (see Figure 7)	3 V	-58	
Crosstalk [‡]	A D	D A	(ooo i igaio i)	4.5 V	-58	-ID
(between switches)	A or B	B or A		1.65 V	-42	dB
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$ $f_{in} = 1 \text{ MHz (sine wave)}$ (see Figure 7)	2.3 V	-42	
				3 V	-42	
				4.5 V	-42	
	С	A or B	C_L = 50 pF, R_L = 600 Ω , f_{in} = 1 MHz (square wave) (see Figure 8)	1.65 V	35	mV
Crosstalk				2.3 V	50	
(control input to signal output)				3 V	70	
				4.5 V	100	
				1.65 V	-58	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	-58	
			f _{in} = 1 MHz (sine wave) (see Figure 9)	3 V	-58	
Feed-through attenuation‡	A D	D A	(See Figure 9)	4.5 V	-58	-ID
(switch off)	A or B	B or A		1.65 V	-42	dB
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	-42	
			f _{in} = 1 MHz (sine wave) (see Figure 9)	3 V	-42	
			(See Figure 9)	4.5 V	-42	
				1.65 V	0.1	
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$	2.3 V	0.025	
			f _{in} = 1 kHz (sine wave) (see Figure 10)	3 V	0.015	
	A - 5	D . A	(555 : .9415 : 10)	4.5 V	0.01	
Sine-wave distortion	A or B	B or A		1.65 V	0.15	%
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$	2.3 V	0.025	
			f _{in} = 10 kHz (sine wave) (see Figure 10)	3 V	0.015	
			(500) (9010 10)	4.5 V	0.01	

 $^{^\}dagger$ Adjust f_{in} voltage to obtain 0 dBm at output. Increase f_{in} frequency until dB meter reads -3 dB. ‡ Adjust f_{in} voltage to obtain 0 dBm at input.

operating characteristics, $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
	FARAWETER	TEST CONDITIONS	TYP	TYP	TYP	TYP	UNII
C _{pd}	Power dissipation capacitance	f = 10 MHz	8	9	9.5	11	pF



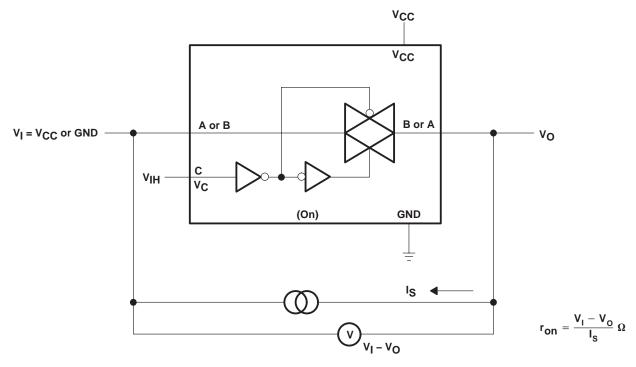


Figure 1. On-State Resistance Test Circuit

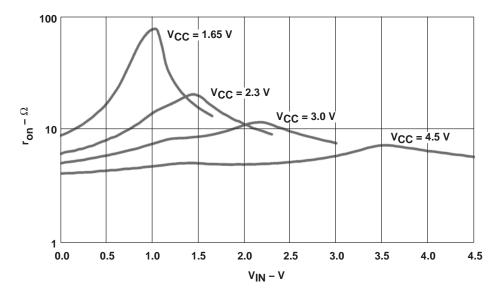


Figure 2. Typical r_{on} as a Function of Input Voltage (V_I) for V_I = 0 to V_{CC}

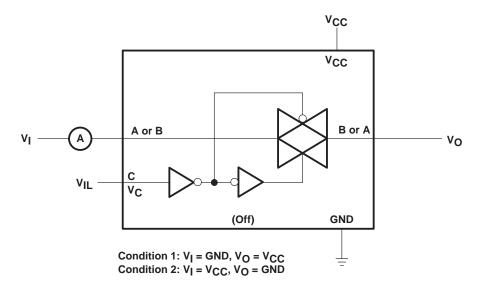


Figure 3. Off-State Switch Leakage-Current Test Circuit

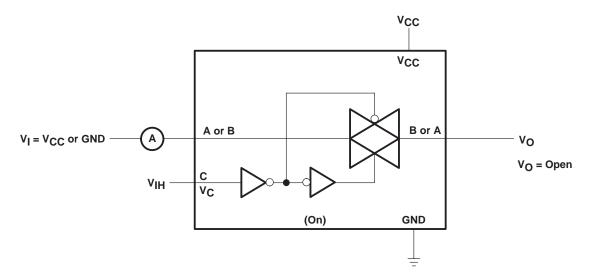
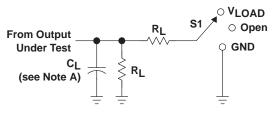


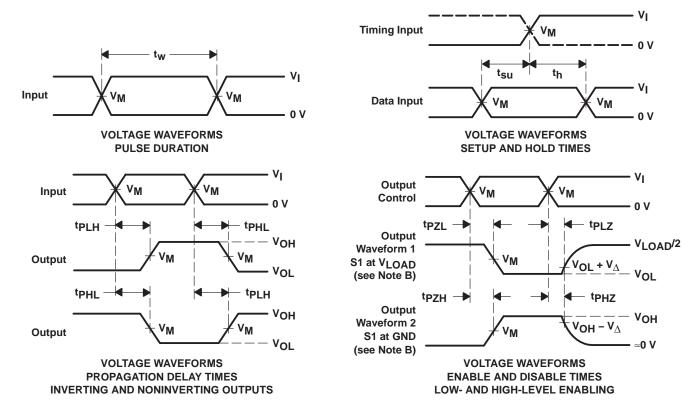
Figure 4. On-State Leakage-Current Test Circuit



TEST	S1
tPLH/tPHL	Open
tPLZ/tPZL	VLOAD
^t PHZ ^{/t} PZH	GND

LOAD CIRCUIT

INPUTS		PUTS		V	0.	D.	V
VCC	٧ _I	t _r /t _f	VM	VLOAD	CL	RL	$v_{\scriptscriptstyle\Delta}$
1.8 V \pm 0.15 V	VCC	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	VCC	≤2 ns	V _{CC} /2	2×VCC	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	VCC	≤2.5 ns	V _{CC} /2	2×V _{CC}	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	VCC	≤2.5 ns	V _{CC} /2	2×VCC	50 pF	500 Ω	0.3 V



- NOTES: A. C_I includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_Ω = 50 Ω.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLz and tpHz are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.
 - H. All parameters and waveforms are not applicable to all devices.

Figure 5. Load Circuit and Voltage Waveforms



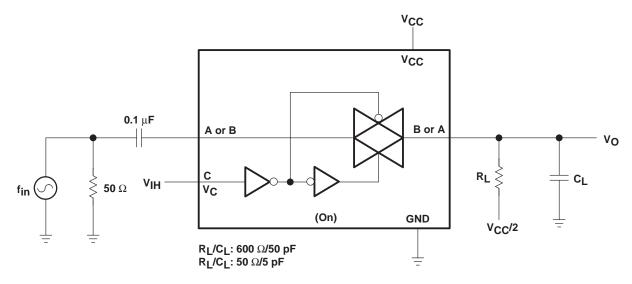


Figure 6. Frequency Response (Switch On)

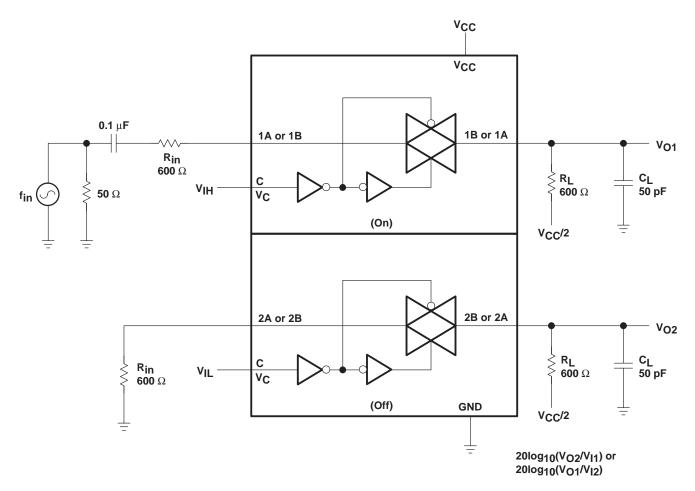


Figure 7. Crosstalk (Between Switches)



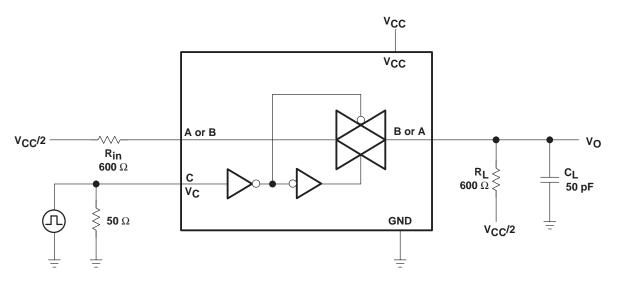


Figure 8. Crosstalk (Control Input, Switch Output)

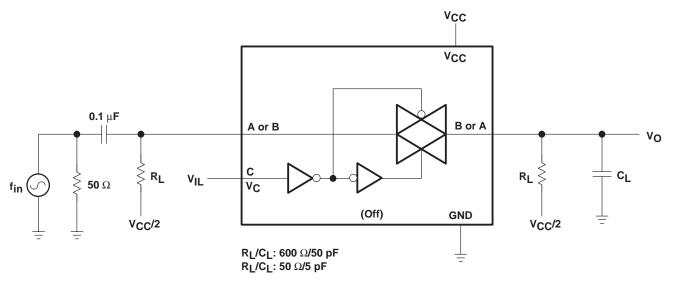


Figure 9. Feed Through (Switch Off)

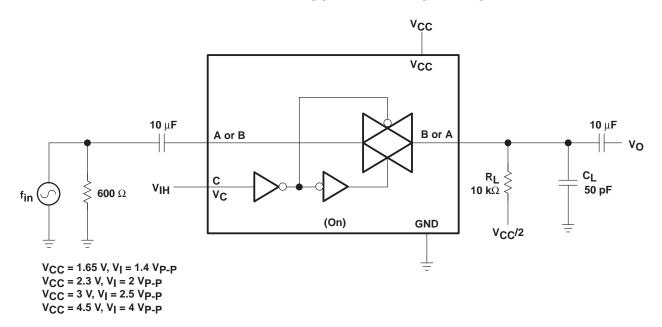
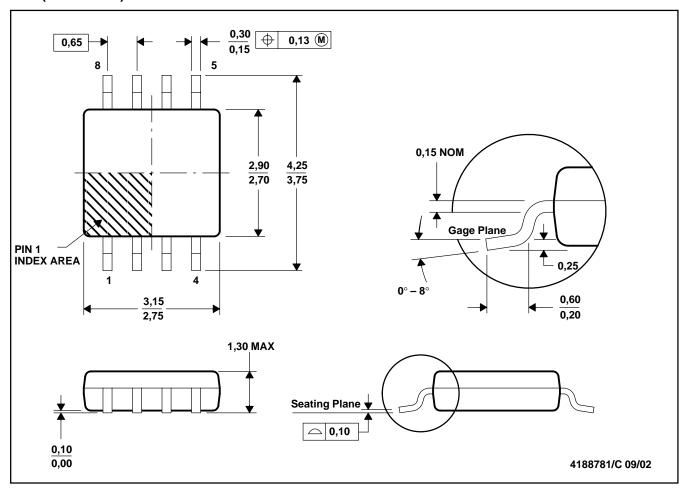


Figure 10. Sine-Wave Distortion

DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE

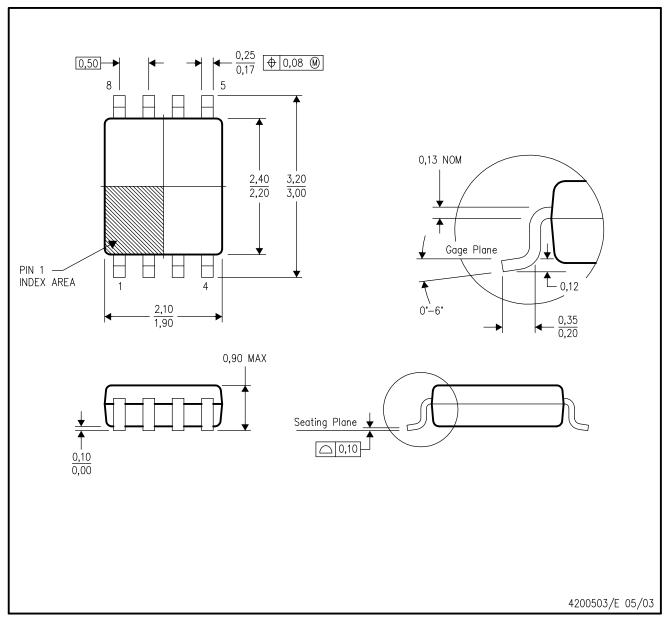


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. Falls within JEDEC MO-187 variation DA.

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



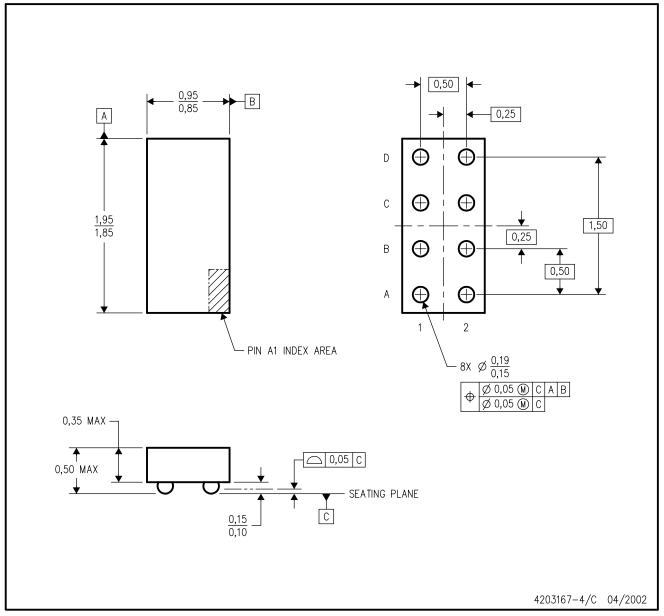
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-187 variation CA.



YEA (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

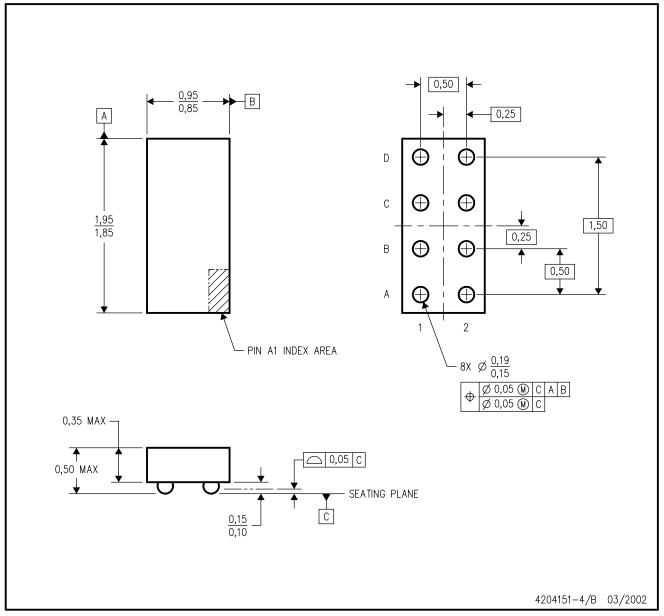
- B. This drawing is subject to change without notice.
- C. NanoStar \mathbf{M} package configuration.
- D. Package complies to JEDEC MO-211 variation EB.
- E. This package is tin-lead (SnPb). Refer to the 8 YZA package (drawing 4204151) for lead-free.

NanoStar is a trademark of Texas Instruments.



YZA (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

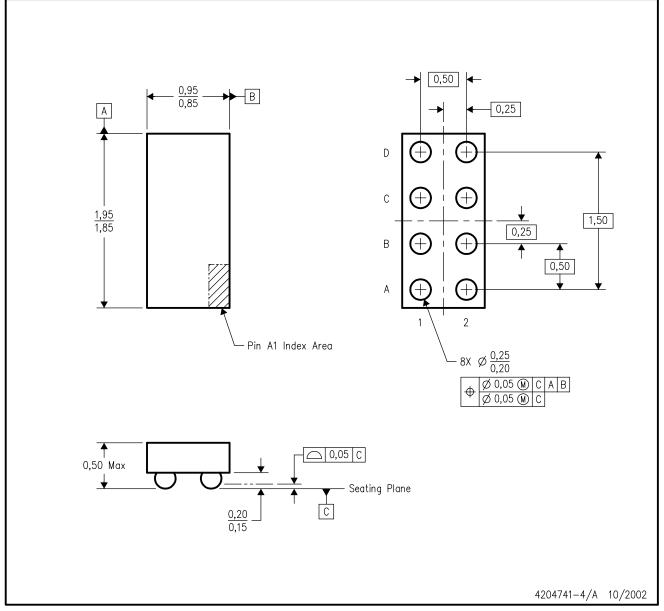
- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. Package complies to JEDEC MO-211 variation EB.
- E. This package is lead-free. Refer to the 8 YEA package (drawing 4203167) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.



YZP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

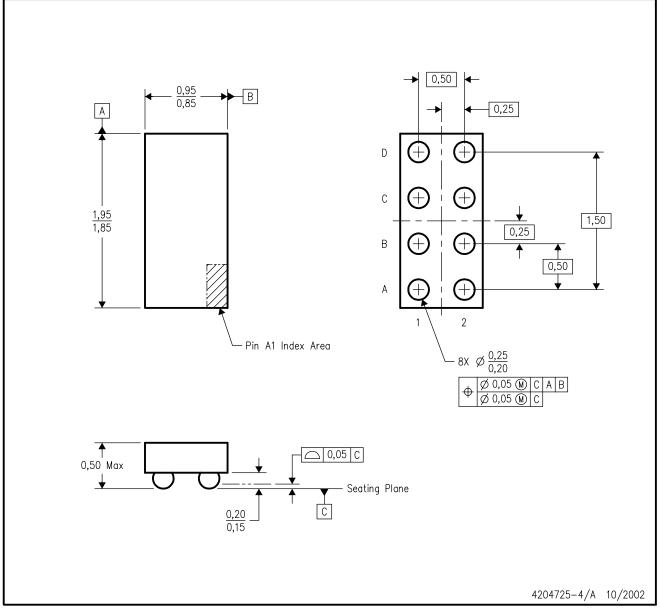
- B. This drawing is subject to change without notice.
- C. NanoFree $^{\text{TM}}$ package configuration.
- D. This package is lead-free. Refer to the 8 YEP package (drawing 4204725) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.



YEP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar \mathbf{M} package configuration.
- D. This package is tin-lead (SnPb). Refer to the 8 YZP package (drawing 4204741) for lead-free.

NanoStar is a trademark of Texas Instruments.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Amplifiers	amplifier.ti.com	Audio	www.ti.com/audio
Data Converters	dataconverter.ti.com	Automotive	www.ti.com/automotive
DSP	dsp.ti.com	Broadband	www.ti.com/broadband
Interface	interface.ti.com	Digital Control	www.ti.com/digitalcontrol
Logic	logic.ti.com	Military	www.ti.com/military
Power Mgmt	power.ti.com	Optical Networking	www.ti.com/opticalnetwork
Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
		Telephony	www.ti.com/telephony
		Video & Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless

Mailing Address: Texas Instruments

Post Office Box 655303 Dallas, Texas 75265

Copyright © 2003, Texas Instruments Incorporated